



Integrated Device Technology, Inc.

# CMOS ASYNCHRONOUS FIFO 32,768 x 9

IDT7207

## FEATURES:

- 32768 x 9 storage capacity
- High-speed: 15ns access time
- Low power consumption
  - Active: 660mW (max.)
  - Power-down: 44mW (max.)
- Asynchronous and simultaneous read and write
- Fully expandable in both word depth and width
- Pin and functionally compatible with IDT720x family
- Status Flags: Empty, Half-Full, Full
- Retransmit capability
- High-performance CMOS technology
- Military product compliant to MIL-STD-883, Class B
- Industrial temperature range (-40°C to +85°C) is available, tested to military electrical specifications

## DESCRIPTION:

The IDT7207 is a monolithic dual-port memory buffer with internal pointers that load and empty data on a first-in/first-out basis. The device uses Full and Empty flags to prevent data overflow and underflow and expansion logic to allow for unlimited expansion capability in both word size and depth.

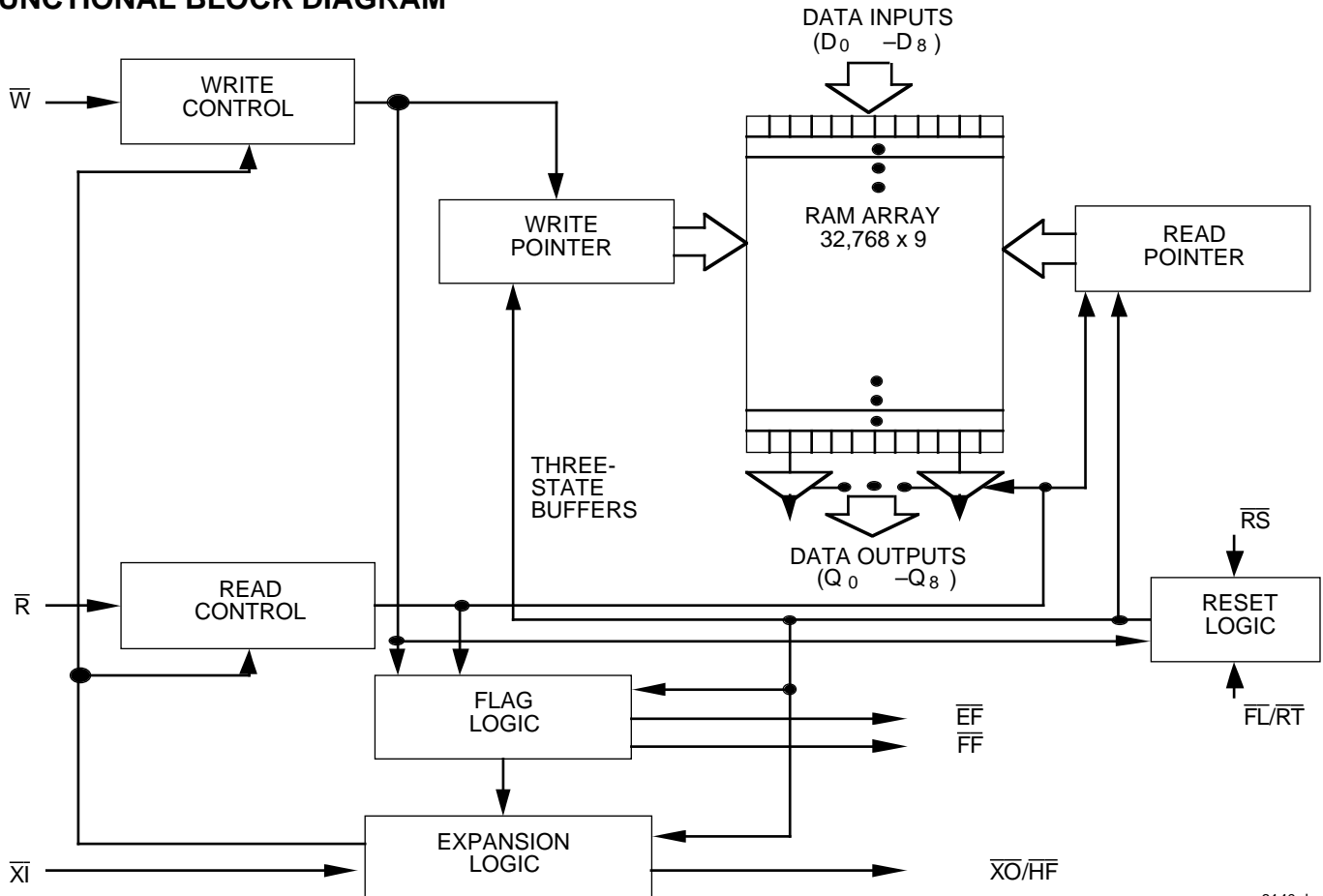
Data is toggled in and out of the device through the use of the Write ( $\bar{W}$ ) and Read ( $\bar{R}$ ) pins.

The device's 9-bit width provides a bit for a control or parity at the user's option. It also features a Retransmit ( $\bar{RT}$ ) capability that allows the read pointer to be reset to its initial position when  $\bar{RT}$  is pulsed LOW. A Half-Full Flag is available in the single device and width expansion modes.

The IDT7207 is fabricated using IDT's high-speed CMOS technology. It is designed for applications requiring asynchronous and simultaneous read/writes in multiprocessing, rate buffering, and other applications.

Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B.

## FUNCTIONAL BLOCK DIAGRAM



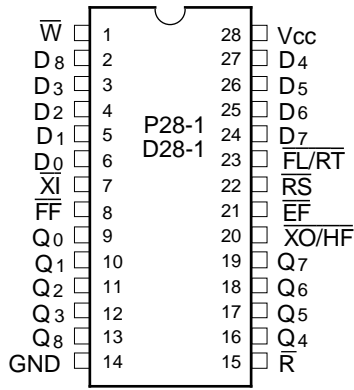
3140 drw 01

The IDT logo is a registered trademark of Integrated Device Technology, Inc.

**MILITARY AND COMMERCIAL TEMPERATURE RANGES**

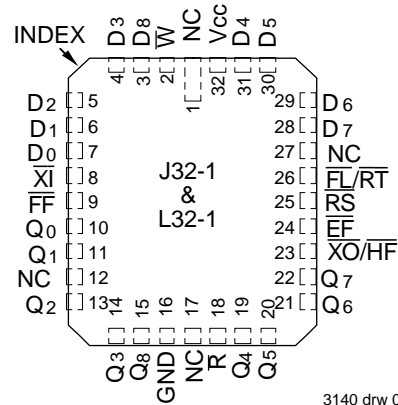
**DECEMBER 1996**

**PIN CONFIGURATIONS**



3140 drw 02

**DIP  
TOP VIEW**



3140 drw 03

**PLCC/LCC  
TOP VIEW**

**ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

Symbol	Rating	Commercial	Military	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	° C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	° C
TSTG	Storage Temperature	-55 to +125	-65 to +155	° C
IOUT	DC Output Current	50	50	mA

**NOTE:** 3140 tbl 01  
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**RECOMMENDED DC OPERATING CONDITIONS**

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCCM	Military Supply Voltage	4.5	5.0	5.5	V
VCCC	Commercial Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH <sup>(1)</sup>	Input High Voltage Commercial	2.0	—	—	V
VIH <sup>(1)</sup>	Input High Voltage Military	2.2	—	—	V
VIL <sup>(1)</sup>	Input Low Voltage Commercial and Military	—	—	0.8	V

**NOTE:** 3140 tbl 02  
1. 1.5V undershoots are allowed for 10ns once per cycle.

**DC ELECTRICAL CHARACTERISTICS FOR THE 7207**

(Commercial: VCC = 5.0V±10%, TA = 0°C to +70°C; Military: VCC = 5.0V±10%, TA = -55°C to +125°C)

Symbol	Parameter	IDT7207 Commercial tA = 15, 20, 25, 35, 50 ns			IDT7207 Military tA = 20, 30, 50 ns			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
ILI <sup>(1)</sup>	Input Leakage Current (Any Input)	-1	—	1	-1	—	1	µA
ILO <sup>(2)</sup>	Output Leakage Current	-10	—	10	-10	—	10	µA
VOH	Output Logic "1" Voltage IOH = -2mA	2.4	—	—	2.4	—	—	V
VOL	Output Logic "0" Voltage IOl = 8mA	—	—	0.4	—	—	0.4	V
ICC1 <sup>(3)</sup>	Active Power Supply Current	—	—	120 <sup>(4)</sup>	—	—	150 <sup>(4)</sup>	mA
ICC2 <sup>(3)</sup>	Standby Current (R=W=RS=FL/RT=VIH)	—	—	12	—	—	25	mA
ICC3(L) <sup>(3)</sup>	Power Down Current (All Input = VCC - 0.2V)	—	—	8	—	—	12	mA

**NOTES:** 3140 tbl 04  
1. Measurements with 0.4 ≤ VIN ≤ VCC.  
2. R ≥ VIH, 0.4 ≤ VOUT ≤ VCC.  
3. ICC measurements are made with outputs open (only capacitive loading).  
4. Tested at f = 20MHz.

## AC ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

(Commercial:  $V_{CC} = 5V \pm 10\%$ ,  $T_A = 0^\circ C$  to  $+70^\circ C$ ; Military:  $V_{CC} = 5V \pm 10\%$ ,  $T_A = -55^\circ C$  to  $+125^\circ C$ )

Symbol	Parameters	Com'l		Com'l & Mil.		Com'l		Military		Com'l		Com'l & Mil.		Unit
		7207L15		7207L20		7207L25		7207L30		7207L35		7207L50		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
tS	Shift Frequency	—	40	—	33.3	—	28.5	—	25	—	22.2	—	15	MHz
tRC	Read Cycle Time	25	—	30	—	35	—	40	—	45	—	65	—	ns
tA	Access Time	—	15	—	20	—	25	—	30	—	35	—	50	ns
tRR	Read Recovery Time	10	—	10	—	10	—	10	—	10	—	15	—	ns
tRPW	Read Pulse Width <sup>(2)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tRLZ	Read LOW to Data Bus LOW <sup>(3)</sup>	5	—	5	—	5	—	5	—	5	—	10	—	ns
tWLZ	Write HIGH to Data Bus Low-Z <sup>(3, 4)</sup>	5	—	5	—	5	—	5	—	10	—	15	—	ns
tDV	Data Valid from Read HIGH	5	—	5	—	5	—	5	—	5	—	5	—	ns
tRHZ	Read HIGH to Data Bus High-Z <sup>(3)</sup>	—	15	—	15	—	18	—	20	—	20	—	30	ns
tWC	Write Cycle Time	25	—	30	—	35	—	40	—	45	—	65	—	ns
tWPW	Write Pulse Width <sup>(2)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tWR	Write Recovery Time	10	—	10	—	10	—	10	—	10	—	15	—	ns
tDS	Data Set-up Time	11	—	12	—	15	—	18	—	18	—	30	—	ns
tDH	Data Hold Time	0	—	0	—	0	—	0	—	0	—	5	—	ns
tRSC	Reset Cycle Time	25	—	30	—	35	—	40	—	45	—	65	—	ns
tRS	Reset Pulse Width <sup>(2)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tRSS	Reset Set-up Time <sup>(3)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tRTR	Reset Recovery Time	10	—	10	—	10	—	10	—	10	—	15	—	ns
tRTC	Retransmit Cycle Time	25	—	30	—	35	—	40	—	45	—	65	—	ns
tRT	Retransmit Pulse Width <sup>(2)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tRTS	Retransmit Set-up Time <sup>(3)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tRSR	Retransmit Recovery Time	10	—	10	—	10	—	10	—	10	—	15	—	ns
tEFL	Reset to EF LOW	—	25	—	30	—	35	—	40	—	45	—	65	ns
tHFH, tFFH	Reset to HF and FF HIGH	—	25	—	30	—	35	—	40	—	45	—	65	ns
tRTF	Retransmit LOW to Flags Valid	—	25	—	30	—	35	—	40	—	45	—	65	ns
tREF	Read LOW to EF LOW	—	15	—	20	—	25	—	30	—	30	—	45	ns
tRFF	Read HIGH to FF HIGH	—	15	—	20	—	25	—	30	—	30	—	45	ns
tRPE	Read Pulse Width after EF HIGH	15	—	20	—	25	—	30	—	35	—	50	—	ns
tWEF	Write HIGH to EF HIGH	—	15	—	20	—	25	—	30	—	30	—	45	ns
tWFF	Write LOW to FF LOW	—	15	—	20	—	25	—	30	—	30	—	45	ns
tWHF	Write LOW to HF Flag LOW	—	25	—	30	—	35	—	40	—	45	—	65	ns
tRHF	Read HIGH to HF Flag HIGH	—	25	—	30	—	35	—	40	—	45	—	65	ns
tWPF	Write Pulse Width after FF HIGH	15	—	20	—	25	—	30	—	35	—	50	—	ns
tXOL	Read/Write LOW to XO LOW	—	15	—	20	—	25	—	30	—	35	—	50	ns
tXOH	Read/Write HIGH to XO HIGH	—	15	—	20	—	25	—	30	—	35	—	50	ns
tXI	XI Pulse Width <sup>(2)</sup>	15	—	20	—	25	—	30	—	35	—	50	—	ns
tXIR	XI Recovery Time	10	—	10	—	10	—	10	—	10	—	10	—	ns
tXIS	XI Set-up Time	10	—	10	—	10	—	10	—	15	—	15	—	ns

### NOTES:

1. Timings referenced as in AC Test Conditions.
2. Pulse widths less than minimum are not allowed.
3. Values guaranteed by design, not currently tested.
4. Only applies to read data flow-through mode.

3140 tbl 05

## AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figure 1

3140 tbl 07

## CAPACITANCE<sup>(1)</sup> (T<sub>A</sub> = +25°C, f = 1.0 MHz)

Symbol	Parameter	Condition	Max.	Unit
C <sub>IN</sub> <sup>(1)</sup>	Input Capacitance	V <sub>IN</sub> = 0V	10	pF
C <sub>OUT</sub> <sup>(1,2)</sup>	Output Capacitance	V <sub>OUT</sub> = 0V	10	pF

### NOTES:

3140 tbl 08

1. This parameter is sampled and not 100% tested.
2. With output deselected.

## SIGNAL DESCRIPTIONS

### Inputs:

**DATA IN (D<sub>0</sub>–D<sub>8</sub>)** — Data inputs for 9-bit wide data.

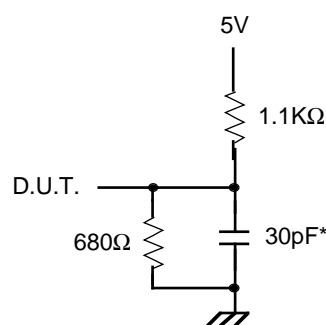
### Controls:

**RESET ( $\overline{RS}$ )** — Reset is accomplished whenever the Reset ( $\overline{RS}$ ) input is taken to a LOW state. During reset, both internal read and write pointers are set to the first location. A reset is required after power-up before a write operation can take place. **Both the Read Enable ( $\overline{R}$ ) and Write Enable ( $\overline{W}$ ) inputs must be in the HIGH state during the window shown in Figure 2 (i.e. tr<sub>SS</sub> before the rising edge of  $\overline{RS}$ ) and should not change until tr<sub>SR</sub> after the rising edge of  $\overline{RS}$ .**

**WRITE ENABLE ( $\overline{W}$ )** — A write cycle is initiated on the falling edge of this input if the Full Flag ( $\overline{FF}$ ) is not set. Data set-up and hold times must be adhered-to, with respect to the rising edge of the Write Enable ( $\overline{W}$ ). Data is stored in the RAM array sequentially and independently of any on-going read operation.

After half of the memory is filled, and at the falling edge of the next write operation, the Half-Full Flag ( $\overline{HF}$ ) will be set to LOW, and will remain set until the difference between the write pointer and read pointer is less-than or equal to one-half of the total memory of the device. The Half-Full Flag ( $\overline{HF}$ ) is reset by the rising edge of the read operation.

To prevent data overflow, the Full Flag ( $\overline{FF}$ ) will go LOW on the falling edge of the last write signal, which inhibits further write operations. Upon the completion of a valid read operation, the Full Flag ( $\overline{FF}$ ) will go HIGH after tr<sub>FF</sub>, allowing a new valid write to begin. When the FIFO is full, the internal write pointer is blocked from  $\overline{W}$ , so external changes in  $\overline{W}$  will not affect the FIFO when it is full.



OR EQUIVALENT CIRCUIT 3140 drw 04

**Figure 1. Output Load**

\*Includes jig and scope capacitances.

**READ ENABLE ( $\overline{R}$ )** — A read cycle is initiated on the falling edge of the Read Enable ( $\overline{R}$ ), provided the Empty Flag ( $\overline{EF}$ ) is not set. The data is accessed on a First-In/First-Out basis, independent of any ongoing write operations. After Read Enable ( $\overline{R}$ ) goes HIGH, the Data Outputs (Q<sub>0</sub> through Q<sub>8</sub>) will return to a high-impedance condition until the next Read operation. When all the data has been read from the FIFO, the Empty Flag ( $\overline{EF}$ ) will go LOW, allowing the “final” read cycle but inhibiting further read operations, with the data outputs remaining in a high-impedance state. Once a valid write operation has been accomplished, the Empty Flag ( $\overline{EF}$ ) will go HIGH after t<sub>WEF</sub> and a valid Read can then begin. When the FIFO is empty, the internal read pointer is blocked from  $\overline{R}$  so external changes will not affect the FIFO when it is empty.

**FIRST LOAD/RETRANSMIT ( $\overline{FU/RT}$ )** — This is a dual-purpose input. In the Depth Expansion Mode, this pin is grounded to indicate that it is the first device loaded (see Operating Modes). The Single Device Mode is initiated by grounding the Expansion In ( $\overline{XI}$ ).

The IDT7207 can be made to retransmit data when the Retransmit Enable Control ( $\overline{RT}$ ) input is pulsed LOW. A retransmit operation will set the internal read pointer to the first location and will not affect the write pointer. The status of the Flags will change depending on the relative locations of the read and write pointers. Read Enable ( $\overline{R}$ ) and Write Enable ( $\overline{W}$ ) must be in the HIGH state during retransmit. This feature is useful when less than 32,768 writes are performed between resets. The retransmit feature is not compatible with the Depth Expansion Mode.

**EXPANSION IN ( $\overline{XI}$ )** — This input is a dual-purpose pin. Expansion In ( $\overline{XI}$ ) is grounded to indicate an operation in the single device mode. Expansion In ( $\overline{XI}$ ) is connected to Expansion Out ( $\overline{XO}$ ) of the previous device in the Depth Expansion or Daisy-Chain Mode.

**Outputs:**

**FULL FLAG ( $\overline{FF}$ )**— The Full Flag ( $\overline{FF}$ ) will go LOW, inhibiting further write operations, when the device is full. If the read pointer is not moved after Reset (RS), the Full Flag ( $\overline{FF}$ ) will go LOW after 32,768 writes.

**EMPTY FLAG ( $\overline{EF}$ )**— The Empty Flag ( $\overline{EF}$ ) will go LOW, inhibiting further read operations, when the read pointer is equal to the write pointer, indicating that the device is empty.

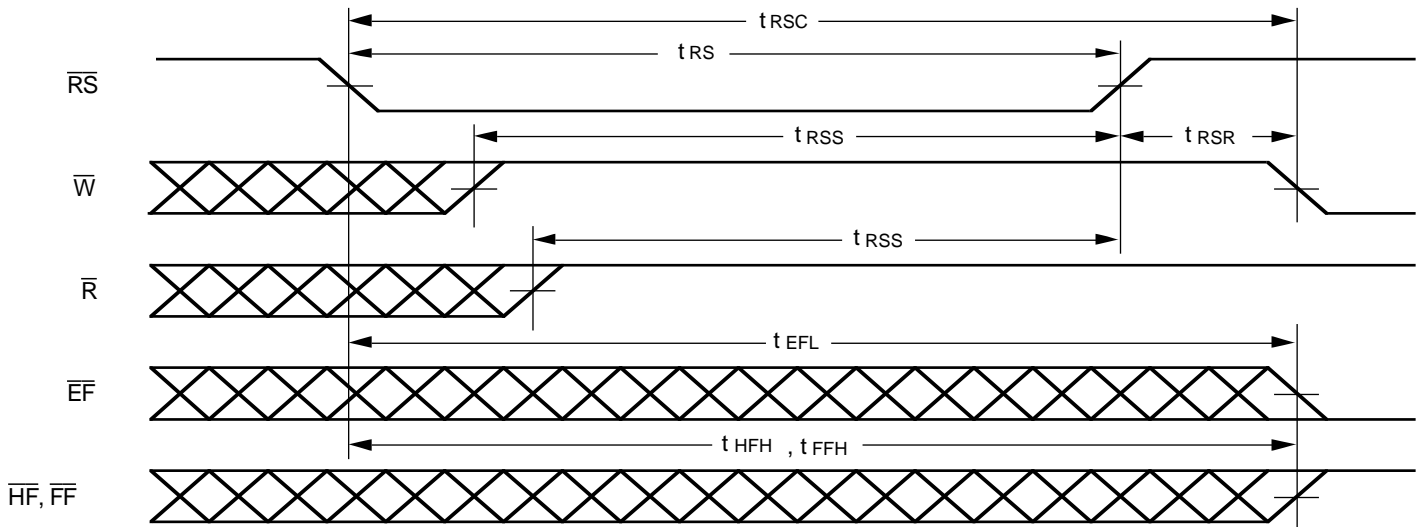
**EXPANSION OUT/HALF-FULL FLAG ( $\overline{XO}/\overline{HF}$ )**— This is a dual-purpose output. In the single device mode, when Expansion In ( $\overline{XI}$ ) is grounded, this output acts as an indication of a half-full memory.

After half of the memory is filled, and at the falling edge of the next write operation, the Half-Full Flag ( $\overline{HF}$ ) will be set to LOW

and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag ( $\overline{HF}$ ) is then reset by the rising edge of the read operation.

In the Depth Expansion Mode, Expansion In ( $\overline{XI}$ ) is connected to Expansion Out ( $\overline{XO}$ ) of the previous device. This output acts as a signal to the next device in the Daisy Chain by providing a pulse to the next device when the previous device reaches the last location of memory. There will be an  $\overline{XO}$  pulse when the Write pointer reaches the last location of memory, and an additional  $\overline{XO}$  pulse when the Read pointer reaches the last location of memory.

**DATA OUTPUTS (Q0-Q8)**— Q0-Q8 are data outputs for 9-bit wide data. These outputs are in a high-impedance condition whenever Read ( $\overline{R}$ ) is in a HIGH state.

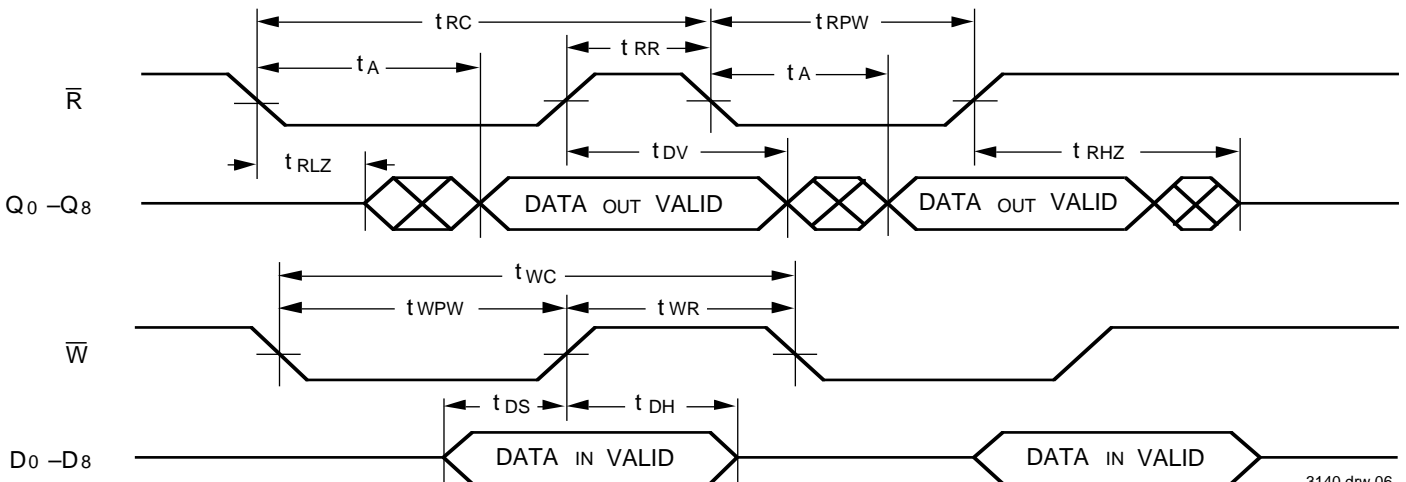


3140 drw 05

**NOTE:**

1.  $\overline{W}$  and  $\overline{R} = V_{IH}$  around the rising edge of  $\overline{RS}$ .

Figure 2. Reset



3140 drw 06

Figure 3. Asynchronous Write and Read Operation

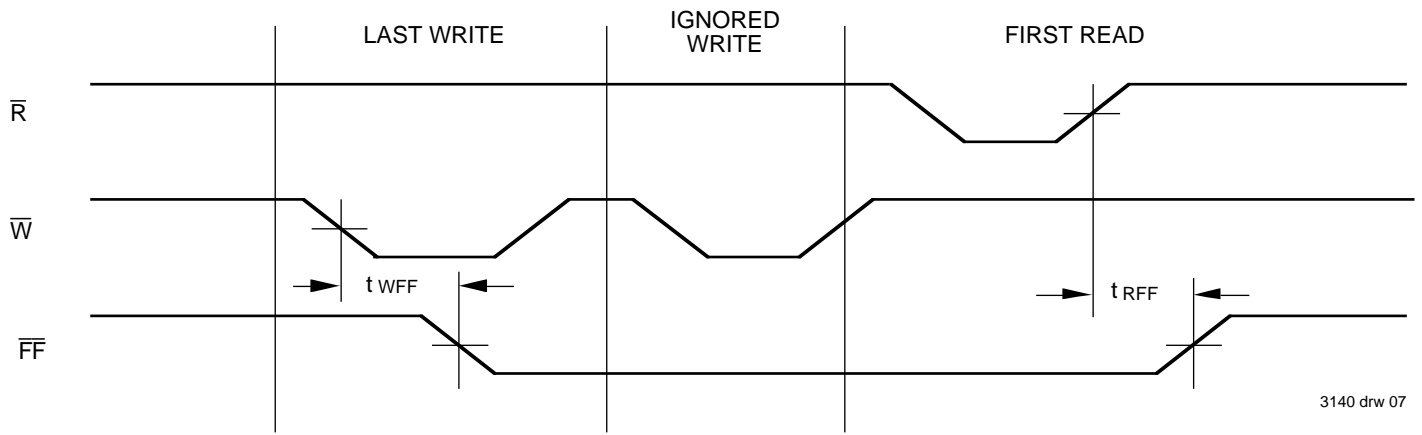


Figure 4. Full Flag Timing From Last Write to First Read

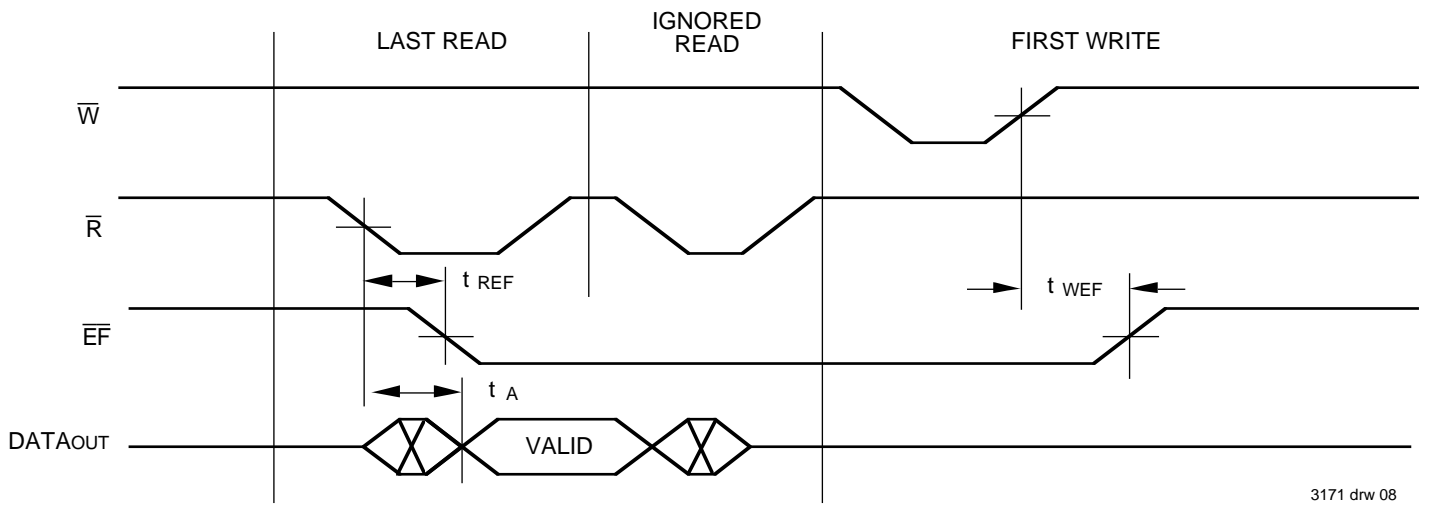
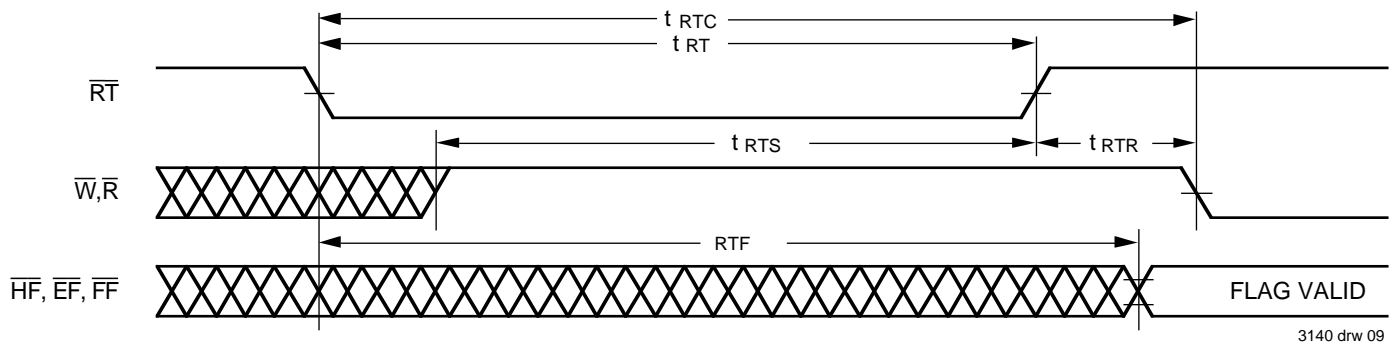


Figure 5. Empty Flag Timing From Last Read to First Write



**NOTE:**

1.  $\overline{EF}$ ,  $\overline{FF}$  and  $\overline{HF}$  may change status during Retransmit, but flags will be valid at  $t_{RTC}$ .

Figure 6. Retransmit

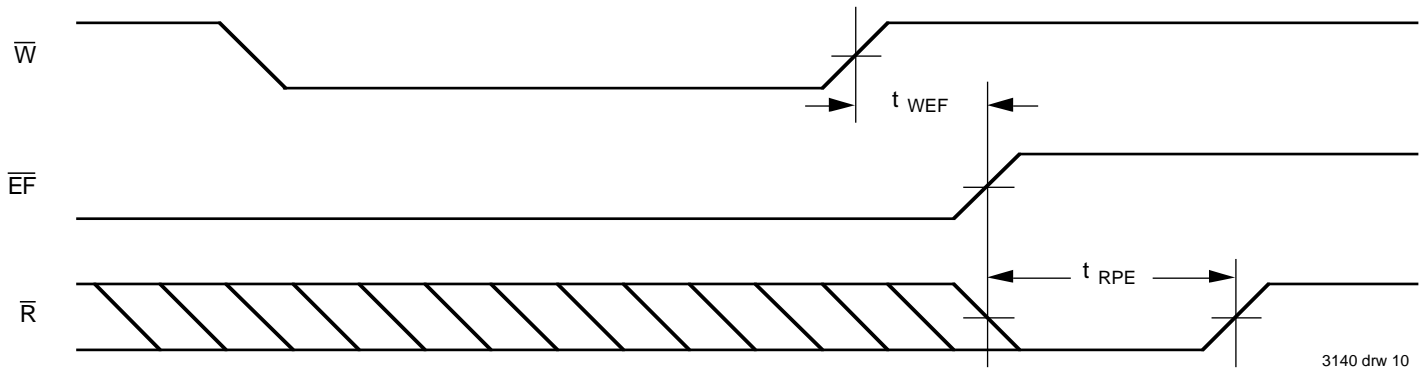


Figure 7. Minimum Timing for an Empty Flag Coincident Read Pulse.

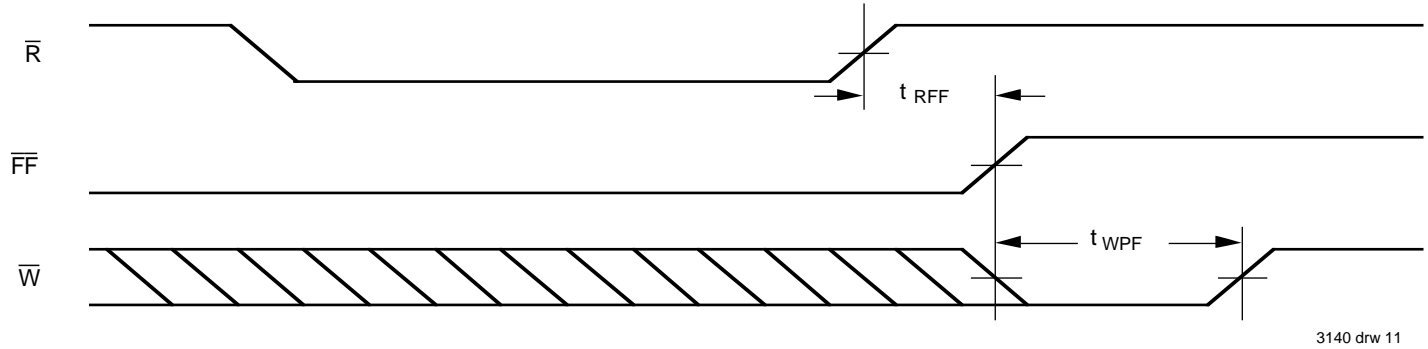


Figure 8. Minimum Timing for a Full Flag Coincident Write Pulse.

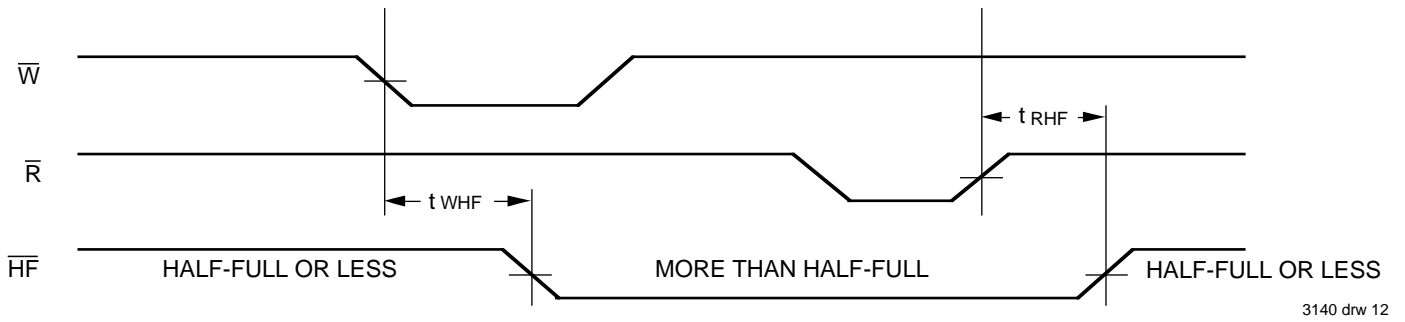


Figure 9. Half-Full Flag Timing

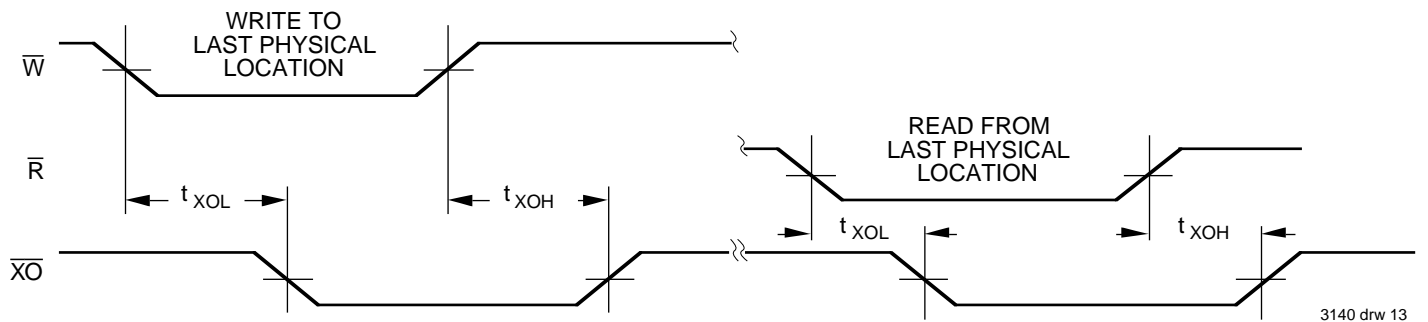


Figure 10. Expansion Out

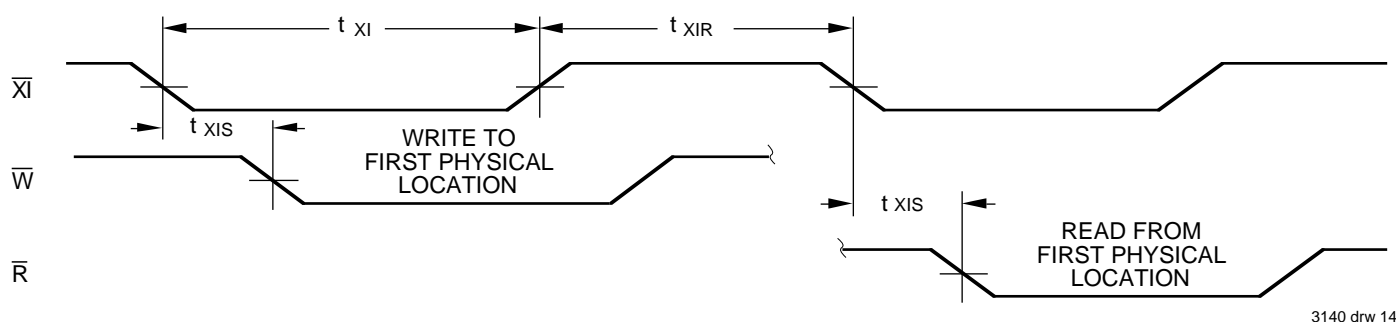


Figure 11. Expansion In

3140 drw 14

## OPERATING MODES:

Care must be taken to assure that the appropriate flag is monitored by each system (i.e.  $\overline{FF}$  is monitored on the device where  $\overline{W}$  is used;  $\overline{EF}$  is monitored on the device where  $\overline{R}$  is used). For additional information, refer to Tech Note 8: *Operating FIFOs on Full and Empty Boundary Conditions* and Tech Note 6: *Designing with FIFOs*.

### Single Device Mode

A single IDT7207 may be used when the application requirements are for 32,768 words or less. The IDT7207 is in a Single Device Configuration when the Expansion In ( $\overline{XI}$ ) control input is grounded (see Figure 12).

### Depth Expansion

The IDT7207 can easily be adapted to applications when the requirements are for greater than 32,768 words. Figure 14 demonstrates Depth Expansion using three IDT7207s. Any depth can be attained by adding additional IDT7207s. The IDT7207 operates in the Depth Expansion mode when the following conditions are met:

1. The first device must be designated by grounding the First Load ( $\overline{FL}$ ) control input.
2. All other devices must have  $\overline{FL}$  in the HIGH state.
3. The Expansion Out ( $\overline{XO}$ ) pin of each device must be tied to the Expansion In ( $\overline{XI}$ ) pin of the next device. See Figure 14.
4. External logic is needed to generate a composite Full Flag ( $\overline{FF}$ ) and Empty Flag ( $\overline{EF}$ ). This requires the ORing of all  $\overline{EF}$ s and ORing of all  $\overline{FF}$ s (i.e. all must be set to generate the correct composite  $\overline{FF}$  or  $\overline{EF}$ ). See Figure 14.
5. The Retransmit ( $\overline{RT}$ ) function and Half-Full Flag ( $\overline{HF}$ ) are not available in the Depth Expansion Mode.

For additional information, refer to Tech Note 9: *Cascading FIFOs or FIFO Modules*.

## USAGE MODES:

### Width Expansion

Word width may be increased simply by connecting the

corresponding input control signals of multiple devices. Status flags ( $\overline{EF}$ ,  $\overline{FF}$  and  $\overline{HF}$ ) can be detected from any one device. Figure 13 demonstrates an 18-bit word width by using two IDT7207s. Any word width can be attained by adding additional IDT7207s (Figure 13).

### Bidirectional Operation

Applications which require data buffering between two systems (each system capable of Read and Write operations) can be achieved by pairing IDT7207s as shown in Figure 16. Both Depth Expansion and Width Expansion may be used in this mode.

### Data Flow-Through

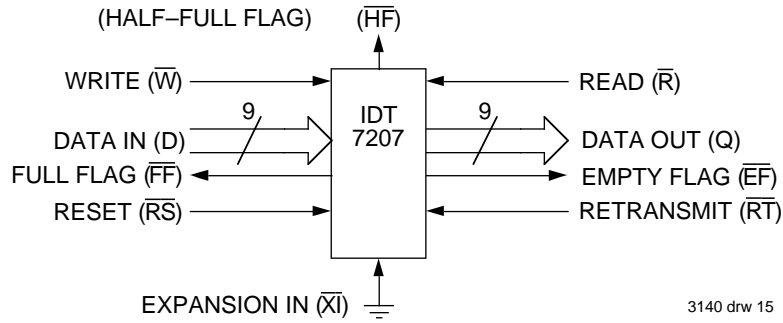
Two types of flow-through modes are permitted, a read flow-through and write flow-through mode. For the read flow-through mode (Figure 17), the FIFO permits a reading of a single word after writing one word of data into an empty FIFO. The data is enabled on the bus ( $t_{WEF} + t_A$ ) ns after the rising edge of  $\overline{W}$ , called the first write edge, and it remains on the bus until the  $\overline{R}$  line is raised from LOW-to-HIGH, after which the bus would go into a three-state mode after  $t_{RHZ}$  ns. The  $\overline{EF}$  line would have a pulse showing temporary deassertion and then would be asserted.

In the write flow-through mode (Figure 18), the FIFO permits the writing of a single word of data immediately after reading one word of data from a full FIFO. The  $\overline{R}$  line causes the  $\overline{FF}$  to be deasserted but the  $\overline{W}$  line being LOW causes it to be asserted again in anticipation of a new data word. On the rising edge of  $\overline{W}$ , the new word is loaded in the FIFO. The  $\overline{W}$  line must be toggled when  $\overline{FF}$  is not asserted to write new data in the FIFO and to increment the write pointer.

### Compound Expansion

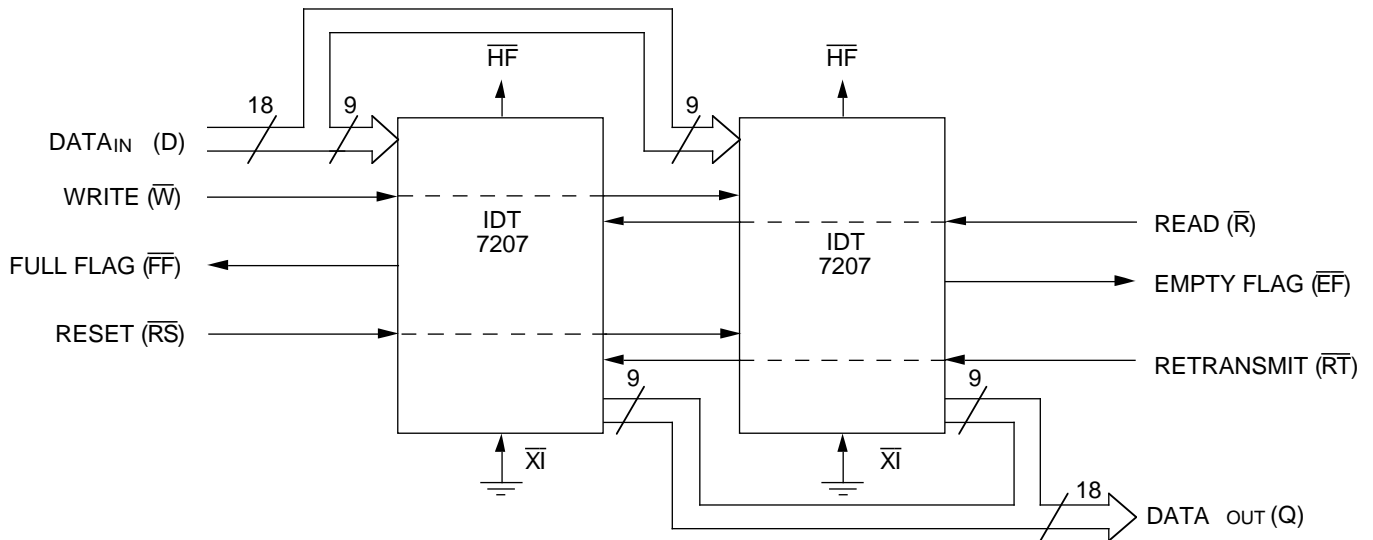
The two expansion techniques described above can be applied together in a straightforward manner to achieve large FIFO arrays (see Figure 15).





3140 drw 15

Figure 12. Block Diagram of 32,768 x 9 FIFO Used in Single Device Mode



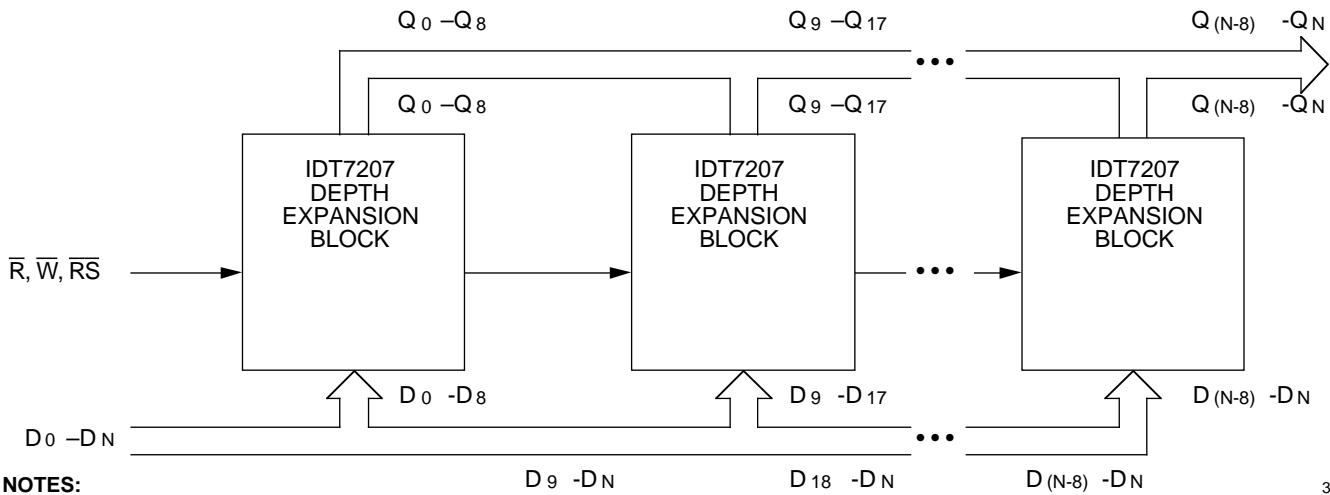
3140 drw 16

**NOTE:**

1. Flag detection is accomplished by monitoring the  $\overline{FF}$ ,  $\overline{EF}$  and  $\overline{HF}$  signals on either (any) device used in the width expansion configuration. Do not connect any output signals together.

Figure 13. Block Diagram of 32,768 x 18 FIFO Memory Used in Width Expansion Mode

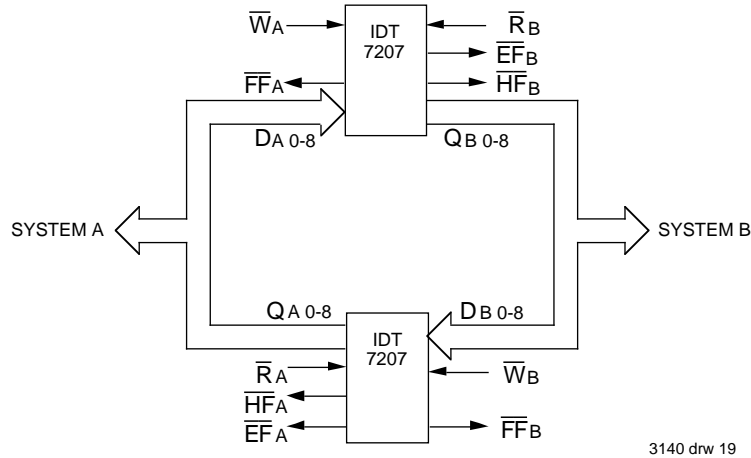




- NOTES:**  
 1. For depth expansion block see section on Depth Expansion and Figure 14.  
 2. For Flag detection see section on Width Expansion and Figure 13.

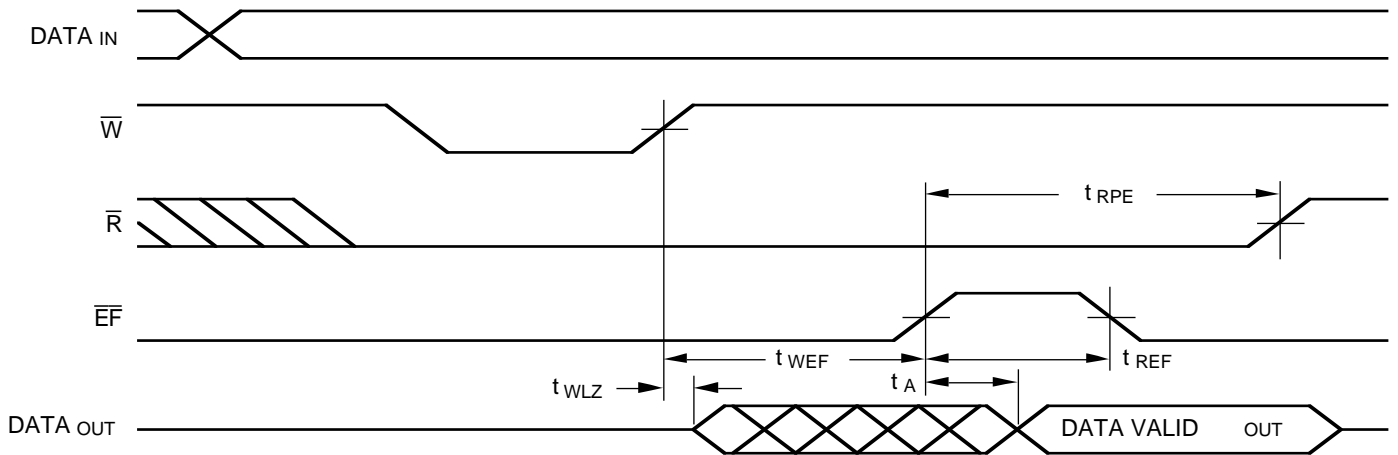
3140 drw 18

Figure 15. Compound FIFO Expansion



3140 drw 19

Figure 16. Bidirectional FIFO Operation



3171 drw 20

Figure 17. Read Data Flow-Through Mode

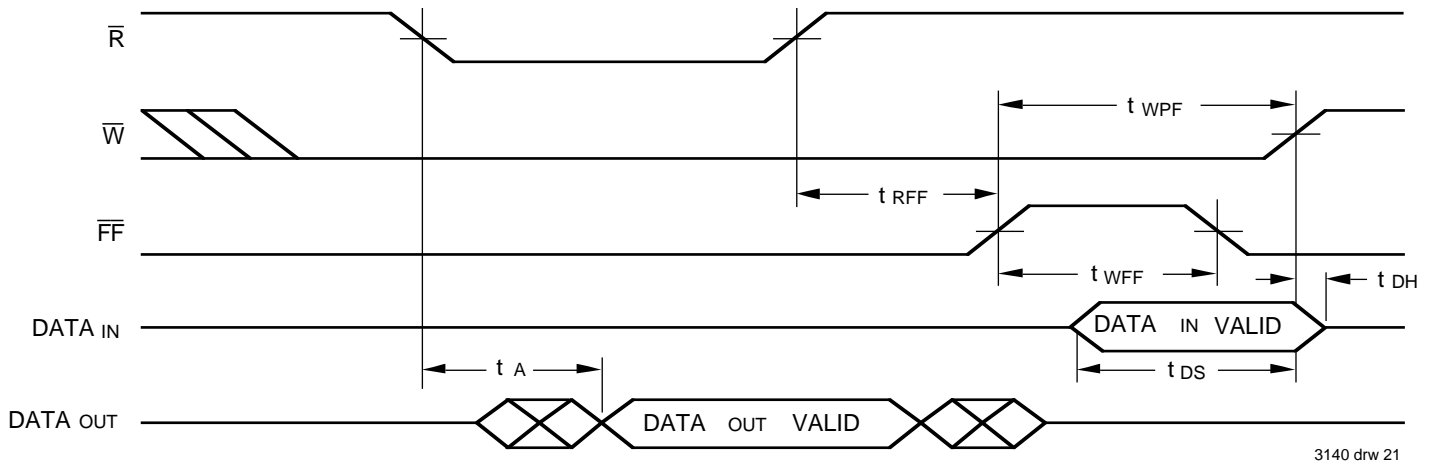


Figure 18. Write Data Flow-Through Mode

3140 drw 21

### ORDERING INFORMATION

IDT	XXXX Device Type	X Power	XX Speed	X Package	X Process/ Temperature Range	
					Blank	Commercial (0°C to +70°C)
					B	Military (-55°C to +125°C) Compliant to MIL-STD-883, Class B
					P	Plastic DIP
					D	Ceramic DIP
					J	Plastic Leaded Chip Carrier
					L	Leadless Chip Carrier (Military only)
					15	Commercial Only
					20	Commercial Only
					25	Commercial Only
					30	Military Only
					35	Commercial Only
					50	Commercial Only
					L	Low Power
					7207	32,768 x 9 FIFO

Access Time ( $t_A$ )  
Speed in ns

3140 drw 22